
2SC4366

Silicon NPN Epitaxial

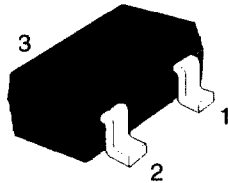
HITACHI

Application

Low Frequency amplifier

Outline

MPAK



1. Emitter
2. Base
3. Collector

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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	60	V
Collector to emitter voltage	V_{CEO}	50	V
Emitter to base voltage	V_{EBO}	15	V
Collector current	I_C	300	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	60	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	50	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	15	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	1	μA	$V_{CB} = 50 \text{ V}, I_E = 0$
Base to emitter voltage	V_{BE}	—	—	0.75	V	$V_{CE} = 6 \text{ V}, I_C = 1 \text{ mA}$
DC current transfer ratio	h_{FE1}	800	—	2000		$V_{CE} = 6 \text{ V}, I_C = 100 \text{ mA}$ (pulse)
	h_{FE2}	500	—	—		$V_{CE} = 6 \text{ V}, I_C = 1 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.3	V	$I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$ (pulse)

Note: Marking is "Z1-".

